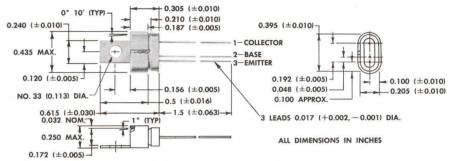
# TYPE 2N243 N-P-N GROWN JUNCTION SILICON TRANSISTOR



Texas Instruments Type 2N243 N-P-N grown junction *silicon* transistor is especially designed for use in audio or servo amplifier stages requiring medium power output. Beta is limited to a 3 to 1 spread, permitting closer control in circuit design. The large energy gap of silicon permits operation at ambient temperatures up to  $150^{\circ}$ C. Each unit is thoroughly temperature cycled. This process consists of four temperature shock cycles from  $-55^{\circ}$ C to  $+150^{\circ}$ C and four cycles at 95% relative humidity from  $-55^{\circ}$ C to  $+75^{\circ}$ C. In addition, the hermetic seal is checked by vacuum testing. Every unit is completely tested for design characteristics and undergoes a rigorous tumble test to check for mechanical reliability.

#### mechanical data

Metal case with glass-to-metal hermetic seal between case and leads. Approximate weight is 2 grams.



#### absolute maximum ratings at 25°C case temperature [except where advanced temperatures are indicated]

Collector	Voltage Refe	erred	to B	ase							60 v
Collector	Current .					4					60 ma
Collector	Dissipation										750  mw
	at 100°C										300  mw
	at 125°C	} .									$150  \mathrm{mw}$

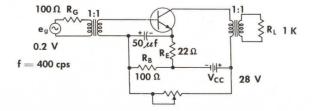
#### junction temperature

### typical design characteristics at $T_j = 25^{\circ}C$

		test co	onditions	min.	design center	max.	unit	
BVco	Collector Breakdown Voltage	$I_C = 50 \text{ uA}$	$I_E = 0$	60	_	_	Volt	
Ico	Collector Cutoff Current	$V_{CB} = 30 \text{ V}$	$I_E = 0$		_	1	$\mu$ A	
I <sub>CO</sub> V <sub>BE</sub>	Bias Voltage	$I_B = 3 \text{ mA}$	$I_{\rm C} = 20  \rm mA$	_	_	1	Volt	
Rec	Collector Saturation Resistance	$I_B = 3  \text{mA}$	$I_C = 20 \text{ mA}$	_	_	350	Ohm	
hib	Input Impedance	$V_{CB} = 10 V$	$I_{\rm E} = -5  \rm mA$		12	30	Ohm	
hrb	Reverse Voltage Transfer Ratio	$V_{CB} = 10 V$	$I_{\rm F} = -5  \rm mA$	_	60	300	X10-	
hfb	Forward Current Transfer Ratio	$V_{CB} = 10 V$	$I_F = -5 \mathrm{mA}$	-0.9	-0.94	-0.968	_	
h <sub>ib</sub> h <sub>rb</sub> h <sub>fb</sub> PG <sub>e</sub>	Power Gain*	$V_{CB} = 28 V$	$I_{\rm C} = 20  \rm mA$	30	_	_	db	

<sup>\*</sup> As measured in the circuit shown below.

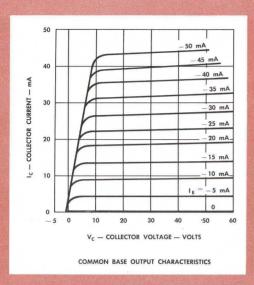
test circuit

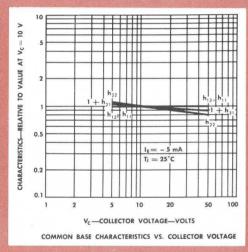


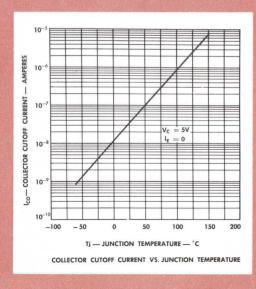
LICENSED UNDER BELL SYSTEM PATENTS

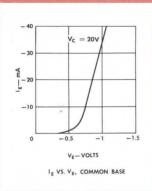
## **TYPE 2N243**

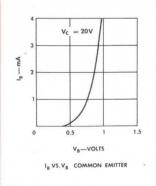
#### TYPICAL CHARACTERISTICS

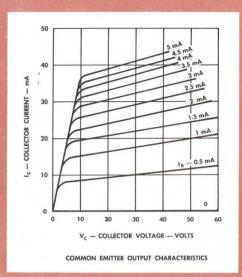


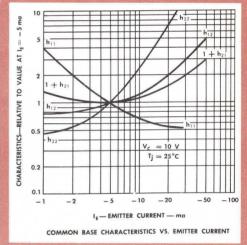


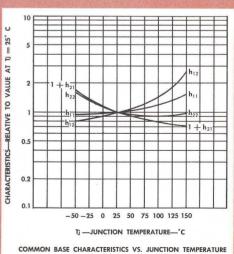












TO SUPPLY THE BEST PRODUCTS POSSIBLE, TEXAS INSTRUMENTS RESERVES THE RIGHT TO MAKE CHANGES AT ANY TIME IN ORDER TO IMPROVE DESIGN.